



BSS138K

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
50V	3.5Ω @ V <sub>GS</sub> = 10V	0.31A

## **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Load Switch

#### **50V N-CHANNEL ENHANCEMENT MODE MOSFET**

### **Features**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts gualified to AEC-Q101, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.
- https://www.diodes.com/guality/product-definitions/

# **Mechanical Data**

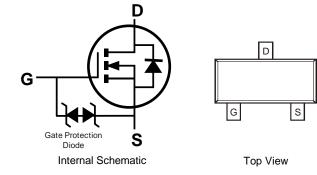
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)







Top View



### Ordering Information (Note 4)

Ì	Part Number	Case	Packaging			
		Case	i aundyiliy			
	BSS138K-7	SOT23	3,000/Tape & Reel			
	BSS138K-13	SOT23	10,000/Tape & Reel			
Notes: 1. No purposely added lead, Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.						

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/guality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# Marking Information

38K	ΥW

38K = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$ = Year (ex: G = 2019) M = Month (ex: 9 = September)

#### Date Code Key

Date Code Rey												
Year	2018	201	9	2020	2021	202	22	2023	2024	20	25	2026
Code	F	G		Н		J		К	L	Ν	Λ	Ν
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	50	V	
Gate-Source Voltage	V <sub>GSS</sub>	±20	V		
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V Stead State		T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	0.31 0.25	А
Maximum Continuous Body Diode Forward Curre	ent (Note 6)	Is	0.5	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle =	1%)	I <sub>DM</sub>	0.8	А	

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.38	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>0JA</sub>	338	°C/W
Total Power Dissipation (Note 6)		PD	0.54	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>0JA</sub>	237	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

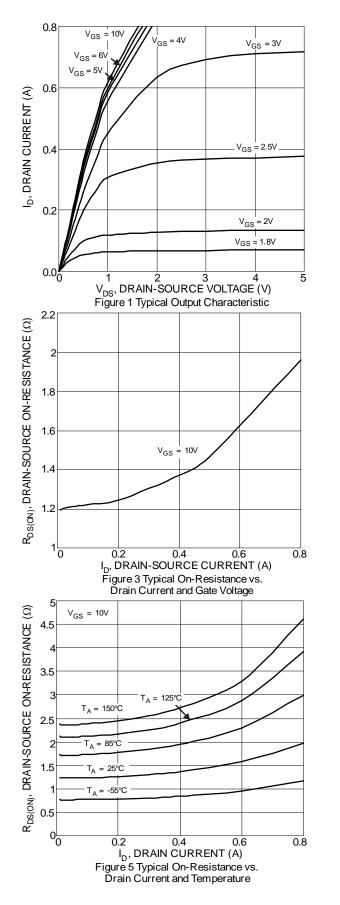
Characteristic	Symbol	Min	Тур	Мах	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage		50	_		V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current $T_J = +25^{\circ}C$	I <sub>DSS</sub>	—	_	1	μA	$V_{DS} = 50V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	—	_	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.5	1.1	1.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	1.3	3.5	Ω	$V_{GS} = 10V, I_D = 0.22A$	
Diode Forward Voltage	V <sub>SD</sub>	—	0.8	1.2	V	$V_{GS} = 0V, I_D = 0.22A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance		_	23.2	—	pF		
Output Capacitance	Coss	—	3.1	_	pF	− V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V − f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	2.2	_	pF		
Gate Resistance	Rg	—	69	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	—	0.45	_	nC		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	—	0.95	—	nC	V <sub>DS</sub> = 25V, I <sub>D</sub> = 0.2A	
Gate-Source Charge	Qgs	—	0.10	_	nC	$v_{DS} = 25v, i_D = 0.2A$	
Gate-Drain Charge	Q <sub>gd</sub>	—	0.14	_	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.2	—	ns		
Turn-On Rise Time	t <sub>R</sub>	—	2.5	_	ns	$V_{DS} = 25V, V_{GS} = 10V,$	
Turn-Off Delay Time	tD(OFF)	—	13.8	—	ns	$R_G = 50\Omega$ , $I_D = 0.2A$	
Turn-Off Fall Time	t <sub>F</sub>	—	7.6	_	ns		
Reverse Recovery Time	t <sub>RR</sub>	—	8.8	—	ns	I <sub>F</sub> = 0.2A, di/dt = 100A/µs	
Reverse Recovery Charge	Q <sub>RR</sub>	_	2.6	_	nC	I <sub>F</sub> = 0.2A, di/dt = 100A/µs	

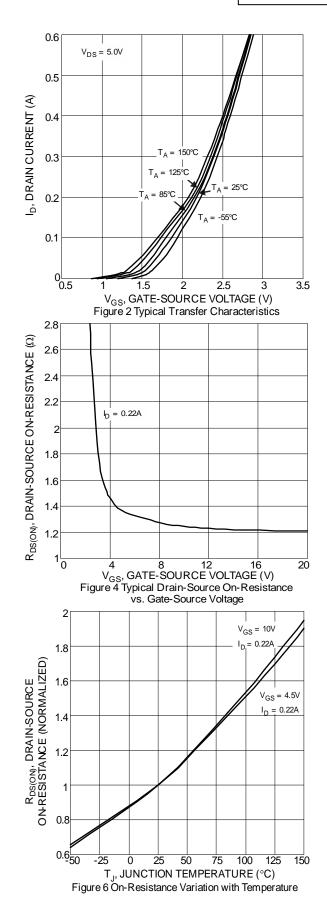
Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided. 7. Short duration pulse test used to minimize self-heating effect.

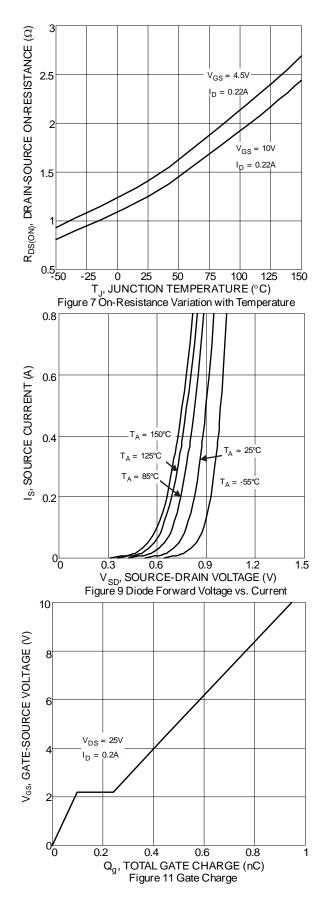
8. Guaranteed by design. Not subject to product testing.

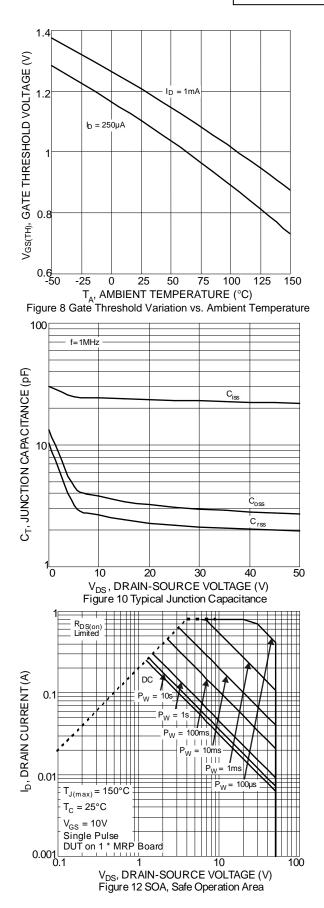




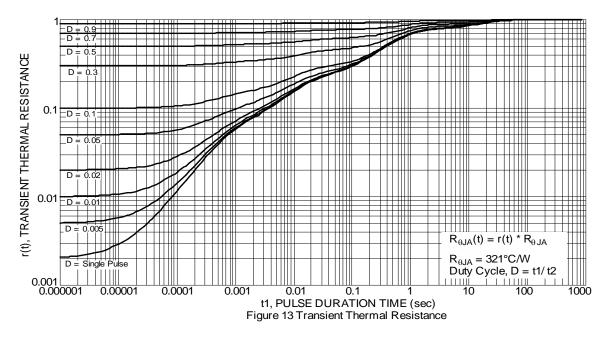








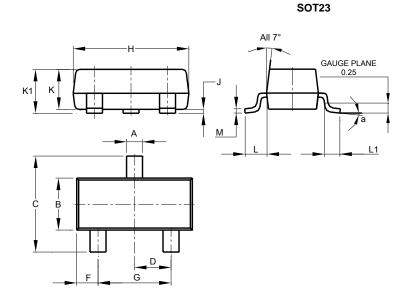






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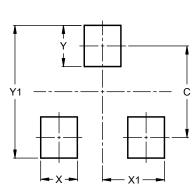
# **Package Outline Dimensions**



	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
c	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	0°	8°						
All	Dimens	ions in	mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Ý	0.9
Y1	2.9

Please see http://www.diodes.com/package-outlines.html for the latest version.



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